BFL4037

ON Semiconductor®

N-Channel Power MOSFET 500V, 16A, 0.43Ω, TO-220F-3FS

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Features

- ON-resistance RDS(on)= 0.33Ω (typ.)
- · 10V drive

• Input capacitance Ciss=1200pF (typ.)

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain to Source Voltage	VDSS		500	V
Gate to Source Voltage	VGSS		±30	V
Drain Current (DC)	I _{Dc} *1	Limited only by maximum temperature Tch=150°C	16	Α
	I _{Dpack*2}	Tc=25°C (Our ideal heat dissipation condition)*3	11	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	60	А
Allowable Power Dissipation	D-		2.0	W
	PD	Tc=25°C (Our ideal heat dissipation condition)*3	40	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C
Avalanche Energy (Single Pulse) *4	EAS		142	mJ
Avalanche Current *5	IAV		16	А

Note:*1 Shows chip capability

- *2 Package limited
- *3 Our condition is radiation from backside.

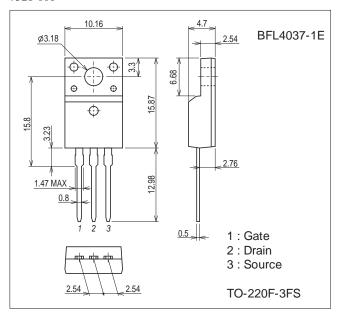
The method is applying silicone grease to the backside of the device and attaching the device to water-cooled radiator made of aluminium.

- *4 VDD=50V, L=1mH, IAV=16A (Fig.1)
- *5 L≤1mH, single pulse

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Package Dimensions

unit : mm (typ) 7528-001



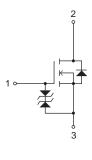
Ordering & Package Information

Device	Device Package Shipping		memo		
BFL4037-1E	TO-220F-3FS SC-67	50 pcs./tube	Pb-Free		

Marking



Electrical Connection

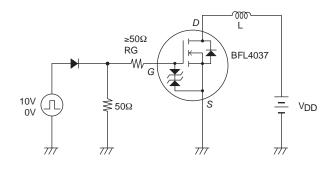


Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
Farameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=10mA, VGS=0V	500			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =400V, V _{GS} =0V			100	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±24V, V _{DS} =0V			±10	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =10V, I _D =1mA	3		5	V
Forward Transfer Admittance	yfs	V _{DS} =10V, I _D =8A	4.5	9		S
Static Drain to Source On-State Resistance	R _{DS} (on)	I _D =8A, V _G S=10V		0.33	0.43	Ω
Input Capacitance	Ciss	V _{DS} =30V, f=1MHz		1200		pF
Output Capacitance	Coss			250		pF
Reverse Transfer Capacitance	Crss			55		pF
Turn-ON Delay Time	t _d (on)	See Fig.2		26.5		ns
Rise Time	tr			78		ns
Turn-OFF Delay Time	t _d (off)			146		ns
Fall Time	tf			57		ns
Total Gate Charge	Qg	V _{DS} =200V, V _{GS} =10V, I _D =16A		48.6		nC
Gate to Source Charge	Qgs			8.2		nC
Gate to Drain "Miller" Charge	Qgd			27.4		nC
Diode Forward Voltage	V _{SD}	I _S =16A, V _{GS} =0V		0.95	1.3	V
Reverse Recovery Time	t _{rr}	See Fig.3		600		ns
Reverse Recovery Charge	Qrr	IS=16A, VGS=0V, di/dt=100A/μs		5000		nC

Fig.1 Unclamped Inductive Switching Test Circuit

Fig.2 Switching Time Test Circuit



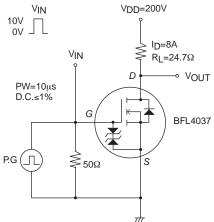
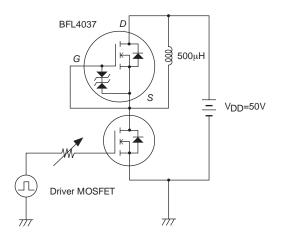
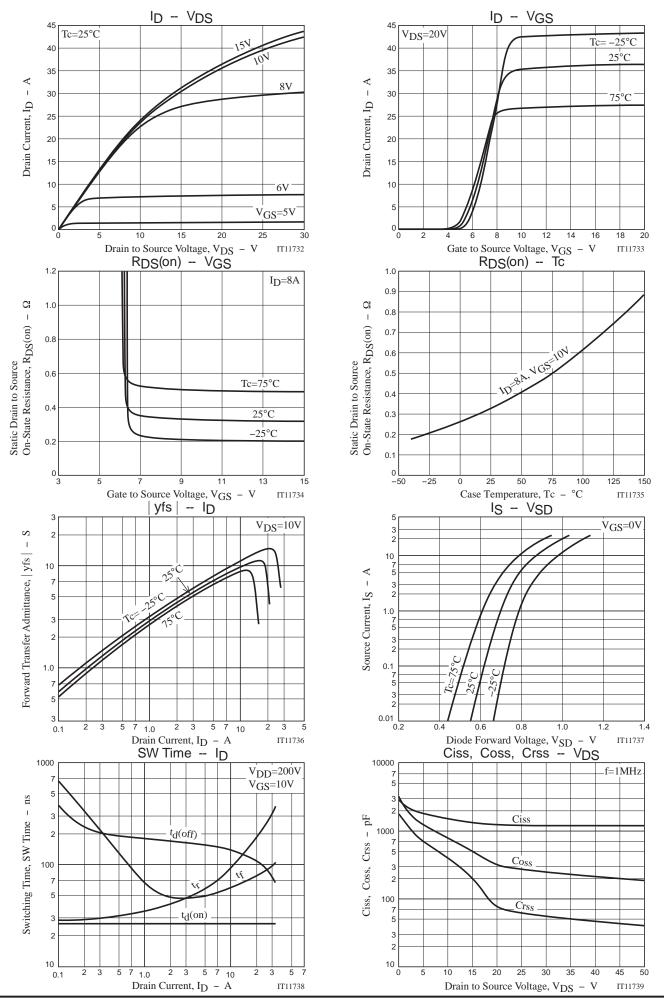
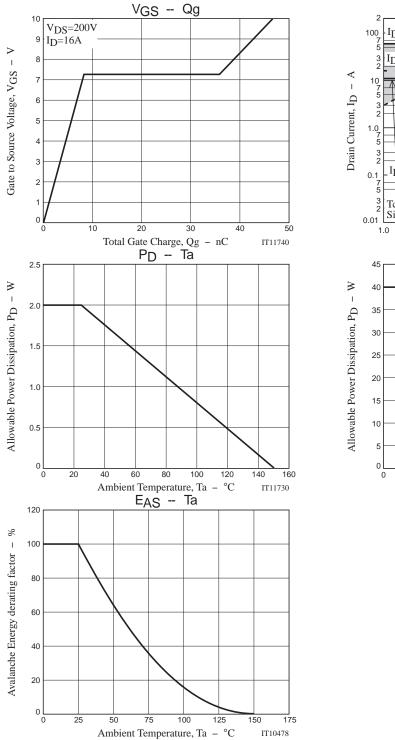
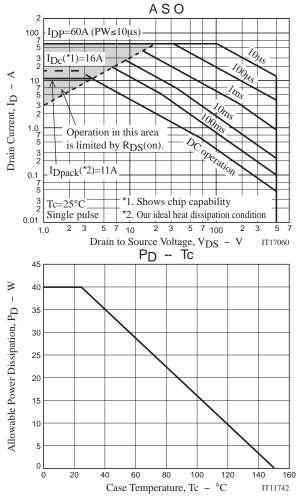


Fig.3 Reverse Recovery Time Test Circuit



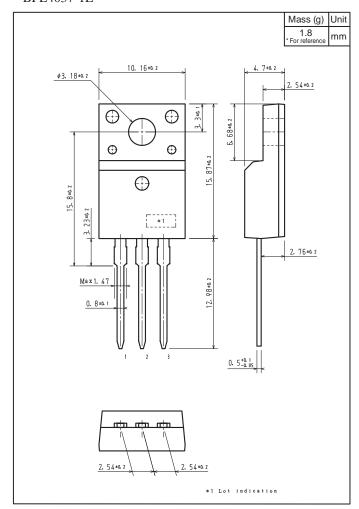






Outline Drawing

BFL4037-1E



Note on usage: Since the BFL4037 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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